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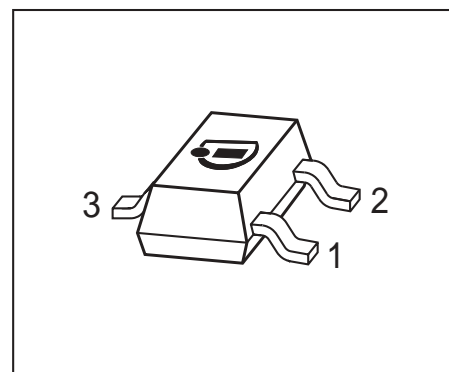
[sales@integrated-circuit.com](mailto:sales@integrated-circuit.com)



**BF775**

### NPN Silicon RF Transistor

- Especially suitable for TV-Sat and UHF tuners
- Pb-free (RoHS compliant) package<sup>1)</sup>
- Qualified according AEC Q101



**ESD (Electrostatic discharge) sensitive device, observe handling precaution!**

Type	Marking	Pin Configuration			Package
BF775	LOs	1 = B	2 = E	3 = C	SOT23

### Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CEO}$	15	V
Collector-emitter voltage	$V_{CES}$	20	
Collector-base voltage	$V_{CBO}$	20	
Emitter-base voltage	$V_{EBO}$	2.5	
Collector current	$I_C$	45	mA
Base current	$I_B$	4	
Total power dissipation <sup>2)</sup> $T_S \leq 48^\circ\text{C}$	$P_{tot}$	280	mW
Junction temperature	$T_j$	150	°C
Ambient temperature	$T_A$	-65 ... 150	
Storage temperature	$T_{stg}$	-65 ... 150	

### Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>3)</sup>	$R_{thJS}$	$\leq 365$	K/W

<sup>1</sup>Pb-containing package may be available upon special request

<sup>2</sup> $T_S$  is measured on the collector lead at the soldering point to the pcb

<sup>3</sup>For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance



**BF775**

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC Characteristics</b>					
Collector-emitter breakdown voltage $I_C = 1 \text{ mA}, I_B = 0$	$V_{(BR)CEO}$	15	-	-	V
Collector-emitter cutoff current $V_{CE} = 20 \text{ V}, V_{BE} = 0$	$I_{CES}$	-	-	10	$\mu\text{A}$
Collector-base cutoff current $V_{CB} = 10 \text{ V}, I_E = 0$	$I_{CBO}$	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 2.5 \text{ V}, I_C = 0$	$I_{EBO}$	-	-	100	$\mu\text{A}$
DC current gain- $I_C = 15 \text{ mA}, V_{CE} = 8 \text{ V}, \text{ pulse measured}$	$h_{FE}$	70	100	140	-


**BF775**
**Electrical Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>AC Characteristics (verified by random sampling)</b>					
Transition frequency $I_C = 15 \text{ mA}$ , $V_{CE} = 8 \text{ V}$ , $f = 500 \text{ MHz}$	$f_T$	3.5	5	-	GHz
Collector-base capacitance $V_{CB} = 10 \text{ V}$ , $f = 1 \text{ MHz}$ , $V_{BE} = 0$ , emitter grounded	$C_{cb}$	-	0.39	0.55	pF
Collector emitter capacitance $V_{CE} = 10 \text{ V}$ , $f = 1 \text{ MHz}$ , $V_{BE} = 0$ , base grounded	$C_{ce}$	-	0.23	-	
Emitter-base capacitance $V_{EB} = 0.5 \text{ V}$ , $f = 1 \text{ MHz}$ , $V_{CB} = 0$ , collector grounded	$C_{eb}$	-	0.64	-	
Noise figure $I_C = 2 \text{ mA}$ , $V_{CE} = 6 \text{ V}$ , $Z_S = Z_{Sopt}$ , $f = 900 \text{ MHz}$ $f = 1.8 \text{ GHz}$	$F$	-	1.4	-	dB
		-	2	-	
Power gain, maximum available <sup>1)</sup> $I_C = 15 \text{ mA}$ , $V_{CE} = 8 \text{ V}$ , $Z_S = Z_{Sopt}$ , $Z_L = Z_{Lopt}$ , $f = 900 \text{ MHz}$ $f = 1.8 \text{ GHz}$	$G_{ma}$	-	16	-	
		-	10.5	-	
Transducer gain $I_C = 15 \text{ mA}$ , $V_{CE} = 8 \text{ V}$ , $Z_S = Z_L = 50\Omega$ , $f = 900 \text{ MHz}$ $f = 1.8 \text{ GHz}$	$ S_{21e} ^2$	-	13	-	dB
		-	7.5	-	

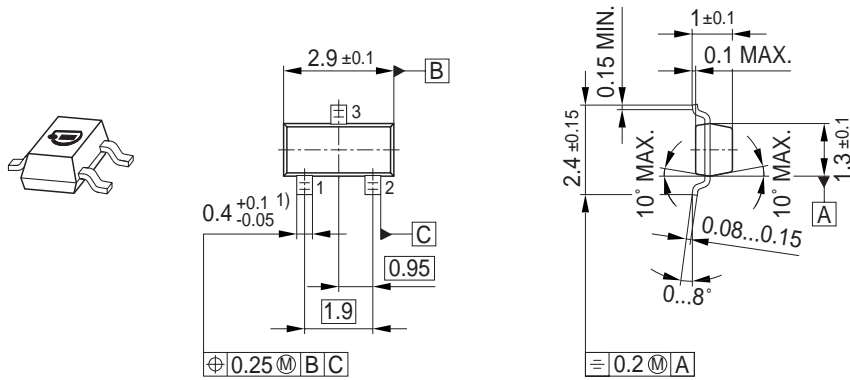
<sup>1</sup> $G_{ma} = |S_{21}/S_{12}| (k-(k^2-1)^{1/2})$



**Package SOT23**

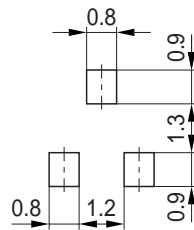
**BF775**

**Package Outline**

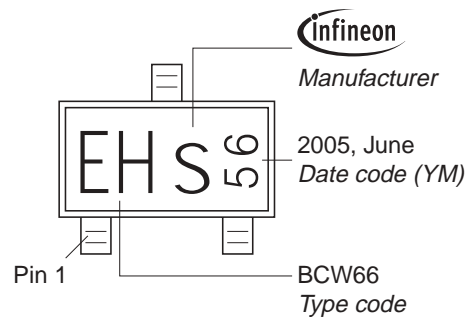


1) Lead width can be 0.6 max. in dambar area

**Foot Print**

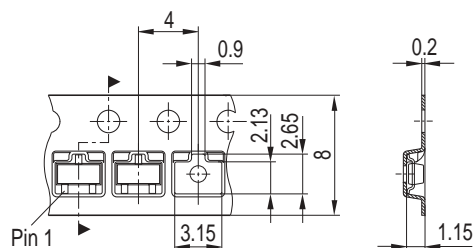


**Marking Layout (Example)**



**Standard Packing**

Reel ø180 mm = 3.000 Pieces/Reel  
 Reel ø330 mm = 10.000 Pieces/Reel





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